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Ultra compact High responsivity photodiodes for >100 Gbaud applications

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Abstract We demonstrated ultra-compact waveguide UTC photodiode with bandwidth efficiency product of 36 GHz on 50Ω load and above 55 GHz on 25Ω load, which allows to reach a bandwidth above 110 GHz with 0.6 A/W responsivity.

Introduction

The fast increase of cloud services leads to a continuous increase of data traffic and transmission experiments are now done at 100 Gbaud and even 200 Gbaud. High bandwidth receiver are of primary importance to limit the complexity of digital signal processing and are widely studied^[1-4]. A classical method to have an improve HF response is to use a matching load resistor to reduce RC time constant and reflection due to impedance mismatch. Using this technique, a receiver module using matching load resistor (resulting in 25Ω effective load) to improve HF response has been demonstrated recently with 145 GHz bandwidth^[1] but at the price of a reduced responsivity and a high PDL (>4 dB). Using the same approach, a bandwidth of 120 GHz with 0.51 A/W responsivity^[2] and 100 GHz with 0.66 A/W responsivity^[3] has been achieved. When looking at intrinsic PD performance, without 50Ω matching resistor, ≈0.5 A/W with 75 GHz bandwidth has been demonstrated^[4]. These diodes however suffer from the length of the input taper (≈1 mm) which increase the overall size of the device.

We have demonstrated in the past short multimode waveguide photodiodes with 0.58 A/W responsivity and an intrinsic 3-dB bandwidth of 50 GHz^[5]. In this paper, we will demonstrate very short photodiodes (0.4x0.5mm²chip size) with a responsivity up to 0.8 A/W for >45 GHz intrinsic bandwidth and 85 GHz on 25Ω load and up to 0.6 A/W for 70 GHz intrinsic bandwidth and >110 GHz bandwidth with matching resistor.

Photodiode design and fabrication

The photodiode (PD) is grown on a semi-insulating substrate using MOVPE (metal organic vapor phase epitaxy) The structure comprises P doped InGaAs absorption layer (0.2 μm) with a inserted between a p+ InP barrier layer (0.5 μm) and a n- InGaAsP collector layer (0.4 μm). This structure, derived from the one described in^[5],

used a multimode diluted waveguide to allow an efficient coupling with a lensed optical fiber. The input facet is etched using ICP dry etching, which allows to realize on wafer AR coating and define a lens^[6] to increase the lateral coupling tolerance. The photodiode junction is etched using a mixed

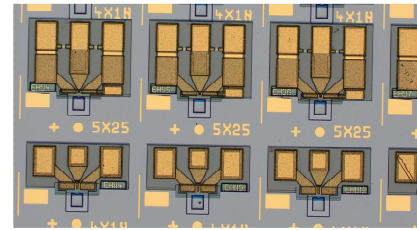


Fig. 1: Optical microscope photograph of UTC wafer with standard photodiode (bottom line) and photodiode with biasing circuit (top line)

of ICP dry etching and wet etching. The main improvements compared to^[5] are optimized epitaxial design with a gradient doping profile in P InGaAs absorber to decrease transit time, an improved process to increase responsivity and decrease parasitic capacitance and the optional implementation of biasing circuit comprising a decoupling capacitor and a matching resistor (Fig.1). The photodiodes are very compact (0.4x0.5 mm² even for devices including integrated biasing circuit) which allows to decrease the individual cost of a photodiode.

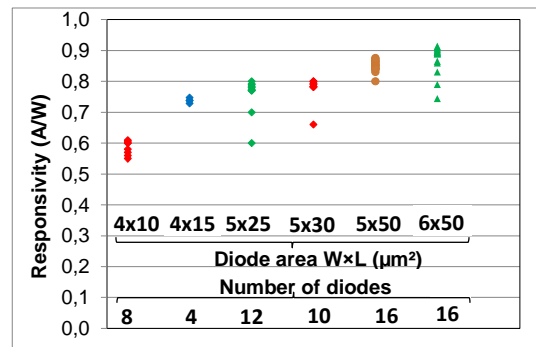


Fig. 2: Responsivity of the UTC photodiode at 1550 nm with the number of diode measured for each geometry

Photodiode characteristics

We implement photodiodes with various dimensions from $4 \times 10 \mu\text{m}^2$ to $6 \times 50 \mu\text{m}^2$. Typical dark current at -2V bias is few nA for all diode size which shows the quality of the passivation of the junction using ICP-SiN_x deposition.

Responsivity measurements are made using a lensed fiber with a mode field diameter (MFD) of $5.5 \mu\text{m}$ and are presented on fig.2. We can notice that the photodiodes presents a high responsivity, up to 0.6 A/W for $4 \times 10 \mu\text{m}^2$ PD to 0.91 A/W for $6 \times 50 \mu\text{m}^2$ PD. For $4 \times 15 \mu\text{m}^2$ PD, the responsivity is already significantly improved compared to $4 \times 10 \mu\text{m}^2$ PD and reach 0.73 A/W which is very promising to reach simultaneously high bandwidth along with high responsivity.

These measurements, made on several photodiodes (4 to 16 depending on diode geometry, as shown in the graph), also show a good reproducibility of the results. The polarization dependence loss (PDL) is very low for all design and stay below 0.2 dB which is, to our best knowledge, state of the art result for such small photodiodes.

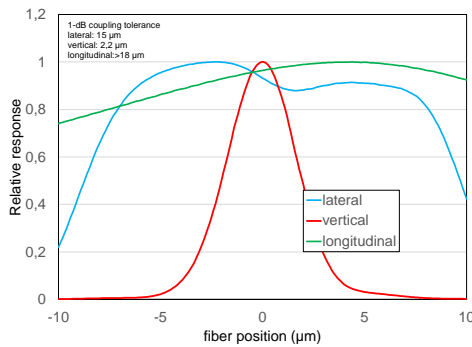


Fig. 3: Coupling tolerance measurements

The use of an integrated lens allows a broad alignment tolerance of $15 \mu\text{m}$ in the lateral direction which simplify the packaging of the photodiode. The tolerance is $2.2 \mu\text{m}$ in the vertical direction and above $18 \mu\text{m}$ in the longitudinal direction.

We then measure the frequency response of our photodiodes using a heterodyne setup. A DC-110 GHz powermeter was used to measure the output HF power of the diode allowing doing a continuous measurement from 0 to 110 GHz. S-parameter based correction using the full S parameters of the photodiode, the probe+bias tee and the powermeter, is used to remove the losses of the probe and bias Tee used for the measurement but also to remove the ripple due to the reflection between the photodiode and the powermeter. We first show on Fig. 4 the frequency response of the photodiodes without matching resistor to find the intrinsic bandwidth of

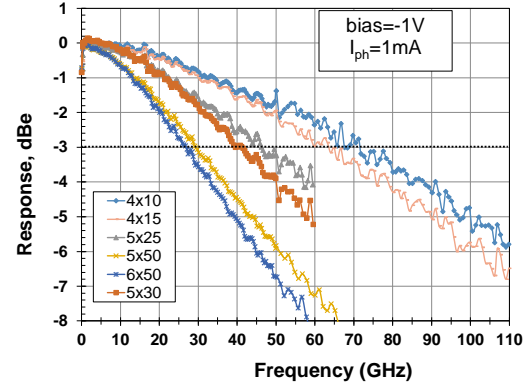


Fig. 4: Influence of the photodiode size on the frequency response

the photodiode on 50Ω load. The measurement was done at 1 mA photocurrent and -1V bias. We can notice that the smallest photodiode ($4 \times 10 \mu\text{m}^2$) present a wide 3 dB bandwidth of 70 GHz with a responsivity of 0.6 A/W, resulting in a wide bandwidth-efficiency product of 34 GHz on 50Ω load. The $4 \times 15 \mu\text{m}^2$ one demonstrates an even higher bandwidth-efficiency product of 37 GHz with a 3 dB bandwidth of 63 GHz and a responsivity of 0.73 A/W. Our photodiode design is very versatile as we obtain on the same wafer 0.8 A/W responsivity and 46 GHz bandwidth with $5 \times 25 \mu\text{m}^2$ PD and even the bandwidth of very large $6 \times 50 \mu\text{m}^2$ PD is still above 25 GHz.

S-parameter measurement allows to extract series resistance and capacitance of the different photodiodes which are respectively 27.8Ω and 16.6 fF for $4 \times 10 \mu\text{m}^2$ photodiode (123 GHz RC cut off), 19.5Ω and 23.1 fF for $4 \times 15 \mu\text{m}^2$ photodiode (99 GHz RC cut off), 11.5Ω and 42.8 fF for $5 \times 25 \mu\text{m}^2$ photodiode (60 GHz RC cut off). From these measurements, we assess an equivalent frequency corresponding to transit time around 80-85 GHz, which is known to be the limiting factor for small diodes. This transit time can easily be improved by reducing collector thickness which is the bandwidth limiting factor.

Fig. 5 presents the influence of the bias voltage on the bandwidth. We can see that even at 0V bias, a wide 3-dB bandwidth of 45 GHz is achieved without responsivity degradation compared to a -1V bias. This is very interesting to simplify photodiode packaging. Then the optimal bias voltage is -1V with 62 GHz bandwidth and the bandwidth decrease to 57 GHz and 53 GHz with respectively -2 and -3V bias voltage. This may results from the electron velocity decrease in III-V semiconductor for electric field is above $\approx 10 \text{ kV/cm}$. This confirms that the transit time in the collector is the major photodiode bandwidth contribution and that the it could be further increased by reducing the

collector thickness.

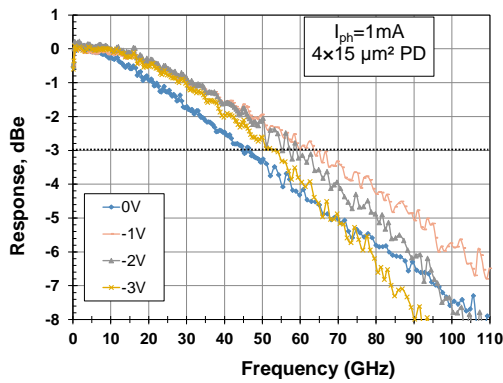


Fig. 5: Influence of the voltage on the frequency response

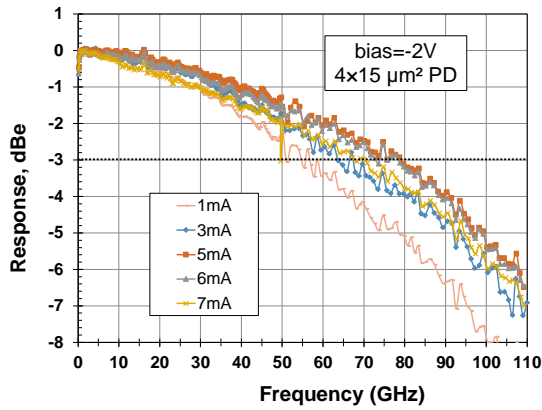


Fig. 6: Influence of the photocurrent on the frequency

UTC are well known for their improved bandwidth under high photocurrent condition, due to negative differential capacitance and electrons overshoot velocity. We measured the frequency response for various photocurrent under -1, -2 and -3 V bias. Fig.6. shows the results under -2V which are the most interesting: the bandwidth increase from 57 GHz at 1 mA to 80 GHz at 5 and 6 mA photocurrent. Interestingly, at 6 mA photocurrent, the responsivity increase by 17% compared to 1 mA photocurrent at 0.85 A/W due to increased temperature in InGaAs absorber.

We implement biasing integrated circuit on samples of 5x25 and 4x10 μm^2 photodiode with decoupling capacitor and matching resistor. Fig.7 shows their frequency response at 1 mA photocurrent and of the 4x10 μm^2 PD at 3 mA. We can notice that due to a 25 Ω effective load (50 Ω matching resistor in parallel with 50 Ω input impedance of the powermeter) the bandwidth is greatly enhanced and is now above 86 GHz for 5x25 μm^2 PD and above 110 GHz for 4x10 μm^2 PD which give records bandwidth-efficiency product of respectively 55 GHz and above 54 GHz on 25 Ω load. With less than 2-dB losses at 110 GHz at 1 mA and only 1 dB losses at 3 mA, we expect a 3-dB bandwidth of at least 120 GHz for small 4x10 μm^2 photodiode.

We observe a small overshoot in the frequency response (around 50 GHz for 5x25 μm^2 PD,

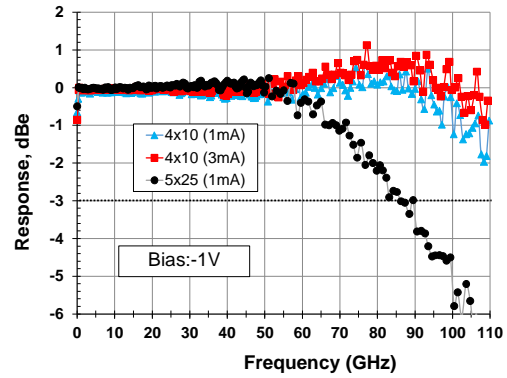


Fig. 7: Frequency response of photodiodes with integrated biasing circuit

around 80 GHz for 4x10 μm^2 PD) which could be due to a transmission line inductive behaviour and can explain that we obtain a 3-dB bandwidth above the transit time limit.

Conclusions

In this paper, we have demonstrated an optimized waveguide UTC design allowing obtaining ultra compact photodiode with very low PDL below 0.2 dB and a very high efficiency-bandwidth product of 36 GHz on 50 Ω load and at least 55 GHz on 25 Ω load. This allows us to realize high speed photodiode with 0.6 A/W responsivity and 70 GHz bandwidth on 50 Ω load. This bandwidth is expanded above 110 GHz bandwidth on 25 Ω load leading to a very high 0.8 A/W responsivity with 86 GHz bandwidth. This is a promising building block for future communication above 100Gbaud and high speed instrumentation equipment. !

Acknowledgements

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References

- [1] P. Runge *et al.*, "broadband 145ghz photodetector module targeting 200gbaud applications", *OFC 2020.*, paper M2.A1.
- [2] A. Beling *et al.*, "miniaturized waveguide-integrated p-i-n photodetector with 120-ghz bandwidth and high responsivity", *IEEE Photon. Technol. Lett.*, Vol.17, no.10; pp2152-2154, 2005.
- [3] H.-G. Bach *et al.*, "InP-based waveguide integrated photodetector with 100 GHz bandwidth", *IEEE J. Sel. Topics Quantum Elecon.*, vol.10 no. 4, pp668-672, 2004.
- [4] G. Zhou *et al.*, "high-power in-p-based waveguide integrated modified uni-traveling-carrier photodiodes", *IEEE J. Lightwave Technol.*, Vol.35, no.4, pp717-721, 2017.

- [5] M. Achouche et al., "high performance evanescent edge coupled waveguide unitraveling-carrier photodiodes for >40-gb/s optical receivers", *IEEE Photon. Technol. Lett*, Vol.16, no.2; pp584-586, 2004.
- [6] M. Achouche et al., "43gb/s balanced photoreceiver using monolithic integrated lensed facet waveguide dual-utc photodiodes" Proc. OECC-ACOFT, WeC-3 (2008).